## CITED BY APPLICANT THAT MAY BE MATERIAL TO THE PROSECUTION OF THE SUBJECT APPLICATION

Applicant:

N.B. Cobb

Attorney Docket No. MEGC121783

Application No.: 10/696,276

Group Art Unit: 2123

Filed:

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Title:

METHOD AND APPARATUS FOR PERFORMING OPC USING MODEL

**CURVATURE** 

## **U.S. PATENT DOCUMENTS**

*Examiner Cite Initials No.	Document No.	Kind Code	Date (mm/dd/yyyy)	Name
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U2	5,825,647	Α	10/20/1998	Tsudaka
U3	6,033,814	Α	03/07/2000	Burdorf et al.
U4	6,080,527	Α	06/27/2000	Huang et al.
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U7	6,249,904	Α	06/19/2001	Cobb
U8	6,269,472	Α	07/31/2001	Garza et al.
U9	6,301,697	Α	10/09/2001	Cobb
U10	6,312,854	Α	11/06/2001	Chen et al.
U11	6,370,679	Α	04/09/2002	Chang et al.

## **FOREIGN PATENT DOCUMENTS**

*Examiner Cite		17.1	Publication Date		English	
	5	Kina	Fublication Date		Abstract	Translation
Initial No	Document No.	Code	(mm/dd/yyyy)	Country	Provided	Provided

None

## OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

*Examiner	Cite	
Initial	No.	
50	O1	Cobb, N., et al., "Experimental Results on Optical Proximity Correction with Variable Threshold Resist Model," Optical Microlithography X, The International Society for Optical Engineering 3051:458-468, March 1997.
<u>Jo</u>	O2	Cobb, N.B., "Fast Optical and Process Proximity Correction Algorithms for Integrated Circuit Manufacturing," Ph.D. dissertation, University of California at Berkeley, Spring 1988, pp. 64-71.
<u>Jo</u>	О3	Cobb, N., et al., "Mathematical and CAD Framework for Proximity Correction," Optical Microlithography IX, The International Society for Optical Engineering 2726: 208-222, March 1996.
10	O4	Benchmark Technologies, OPC Reference Standard (J111A) Reticle, October 12, 1999.
10	O5	"Resolution Enhancement Technologies (OPC/PSM)," July 16, 2002, Mentor Graphics Internet Site, Technical Papers.
10	O6	Randall, J., et al., "Lithography Simulation With Aerial Image - Variable Threshold Resist Model," <i>International Conference on Micro and Nano Engineering 46</i> :59-60, September 1998.
<u>J0</u>	О7	Rieger, M.L. and J.P. Stirniman, "Using Behavior Modeling for Proximity Correction," SPIE Proceedings, The International Society for Optical Engineering, Optical/Laser Microlithography VII 2197:371-376, May 1994.
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JO_	O10	Schellenberg, F.M., "Sub-Wavelength Lithography Using OPC," Semiconductor Fabtech, 9th ed., March 1999.
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ر آ	<u> </u>	O14	Stirniman, J.P. and M.L. Rieger, "Optimizing Proximity Correction for Wafer Fabrication Processes," <i>Proc. SPIE, 14th Annual BACUS Sympoosium on Photomask Technology and Management 2322</i> :239-246, December 1994.
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\*Examiner: Initial if reference considered, whether or not citation is in conformance with M.P.E.P. § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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